

Sheet 1 of 1

Form 1449\*

Atty. Docket No.: 303.356US1

Serial No. 08/902,133

INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT  
(Use several sheets if necessary)

Applicant: Leonard Forbes et al.

Filing Date: July 29, 1997

Group: 2815

U. S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>Dmw</u>	4,460,670	07/01/1984	Ogawa, et al.	430	577	
<u>Dmw</u>	4,657,699	04/01/1987	Nair	252	513	
<u>Dmw</u>	4,738,729	04/01/1998	Yoshida, et al.	136	258	
<u>Dmw</u>	5,145,741	09/01/1992	Quick	428	402	
<u>Dmw</u>	5,604,357	02/18/1997	Hori, T.	257	24	07/11/95
<u>Dmw</u>	5,801,401	09/01/1998	Forbes, L.	257	77	

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No

OTHER DOCUMENTS

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Examiner	<u>V. Martin Wallace</u>	Date Considered	<u>3/3/99</u>
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<i>Jenni</i>	5,714,766	02/03/1998	Chen, et al.	257	20	09/29/95
<i>Jenni</i>	5,754,477	05/19/1998	Forbes	365	185.33	01/29/97

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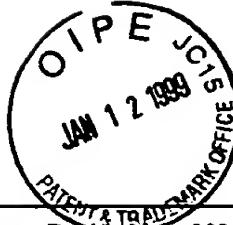
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<i>TMW</i>	5,298,796	03/29/1994	Tawel, R.	307	33	07/08/92
<i>TMW</i>	5,623,442	04/22/1997	Gotou, H., et al.	365	185.08	06/08/94
<i>TMW</i>	5,786,250	07/28/1998	Wu, Z., et al.	438	254	03/14/97

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<i>ALM</i>						

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Vmw	4,893,273	01/09/1990	Usami	365	185 185.04	03/21/86
Vmw	5,111,430	05/05/1992	Morie	365	185 185.24	06/21/90
Vmw	5,260,593	11/09/1993	Lee	257	316	12/10/91
Vmw	5,293,560	03/08/1994	Harari	365	185 185.03	11/03/92
Vmw	5,369,040	11/29/1994	Halvis, et al.	437 438	3 22	04/12/93
Vmw	5,449,941	09/12/1995	Yamazaki, et al.	257	411	10/27/92
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Vmw	5,508,543	04/16/1996	Hartstein, et al.	257	314	04/29/94
Vmw	5,530,581	06/25/1996	Cogan	359	265	05/31/95
Vmw	5,580,380	12/03/1996	Liu, et al.	117	86	01/30/95
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Vmw	3-222367	10/01/1991	Japan	H01L	29/784	
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Vmw	6-302828	10/28/1994	Japan	H01L	29/788	
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Vmw	Alok, D., et al., "Electrical Properties of Thermal Oxide Grown on N-type 6H-Silicon Carbide", <u>Applied Physcis Letters</u> , 64, 2845-2846, (May 23, 1994)
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<i>Vmw</i>	Bengtsson, S., et al., "Applications of Aluminum Nitride Films Deposited by Reactive Sputtering to Silicon-On-Insulator Materials", <u>Japanese J. Applied Physics</u> , 35, 4175-4181, (1996)
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<i>Vmw</i>	Choi, J., et al., "Effect of Deposition Conditions and Pretreatments on the Microstructure of MPECVD Diamond Thin Films", <u>Materials Chemistry and Physics</u> , 45, 176-179, (1996)
<i>Vmw</i>	Clarke, G., et al., "The Infrared Properties of Magnetron-Sputtered Diamond-Like Thin Films", <u>Thin Solid Films</u> , 280, 130-135, (1996)
<i>Vmw</i>	Compagnini, G., et al., "Spectroscopic Characterization of Annealed Si(1-x)C(x) Films", <u>J. Materials Res.</u> , 11, 2269-2273, (Sept. 1996)
<i>Vmw</i>	Dartnell, N., et al., "Reactive Ion Etching of Silicon Carbide (Si(x)C(1-x))", <u>Vacuum</u> , 46, 349-355, (1995)
<i>Vmw</i>	Demichelis, F., et al., "Influence of Doping on the Structural and Optoelectronic Properties of Amorphous and Microcrystalline Silicon Carbide", <u>Journal of Applied Physics</u> , 72, 1327-1333, (Aug. 15, 1992)
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<i>Vmw</i>	Dipert, B., et al., "Flash Memory Goes Mainstream", <u>IEEE Spectrum</u> , 30, 48-52, (1993)

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*V. Marie Wallace*

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<i>Vmws</i>	Friedrichs, P., et al., "Interface Properties of Metal-Oxide-Semiconductor Structures on N-Type 6H and 4H-SiC", <u>J. Applied Physics</u> , 79, 7814-7819, (May 15, 1996)
<i>Vmws</i>	Fujii, T., et al., "Bonding Structures in Highly Photoconductive a-SiC:H Films Deposited by Hybrid-Plasma Chemical Vapor Deposition", <u>Journal of Non-Crystalline Solids</u> , 198-200, 577-581, (1996)
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<i>Vmws</i>	Hamakawa, Y., et al., "Optoelectronics and Photovoltaic Applications of Microcrystalline SiC", <u>Materials Research Society Symposium Proceedings</u> , 164, Boston, MA, 291-301, (11/29-12/1, 1989)
<i>Vmws</i>	He, Z., et al., "Ion-beam-assisted Deposition of Si-carbide Films", <u>Thin Solid Films</u> , 260, 32-37, (1995)
<i>Vmws</i>	Hu, G., "Will Flash Memory Replace Hard Disk Drive?", <u>IEEE Electron Devices Meeting</u> , Session 24, (Dec. 13, 1994)
<i>Vmws</i>	Hwang, J., et al., "High Mobility beta-SiC Epilayer Prepared by Low-pressure Rapid Thermal Chemical Vapor Deposition on a (100) Silicon Substrate", <u>Thin Solid Films</u> , 272, 4-6, (1996)
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<i>Vmws</i>	Kothandaraman, M., et al., "Reactive Ion Etching of Trenches in 6H-SiC", <u>J. Electronic Materials</u> , 25, 875-878, (1996)
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<i>Vmw</i>	Leggieri, G., et al., "Laser Ablation Deposition of Silicon Carbide Films", <u>Applied Surface Science</u> , 96-98, 866-869, (1996)
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<i>Vmw</i>	Liu, J., et al., "Formation of SiC Films on Silicon Field Emitters", <u>Materials Res. Soc. Symp. Proc.</u> , 311, San Francisco, CA, (April 13-15, 1993)
<i>Vmw</i>	Liu, J., et al., "Modification of Si Field Emitter Surfaces by Chemical Conversion to SiC", <u>J. Vac. Sci. Technology</u> , B 12, 717-721, (1994)
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<i>Vmw</i>	McLane, G., et al., "High Etch Rates of SiC in Magnetron Enhanced SF(6) Plasmas", <u>Applied Phys. Lett.</u> , 68, 3755-3757, (June 1996)
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<i>Vmw</i>	Pankove, J., "Photoelectric Emission", <u>In: Optical Processes in Semiconductors</u> , Dover Publications Inc., New York, 287-301, (1971)
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*Vernon Martin Wallace*

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Examiner

*V. Martin Wallace*

Date Considered

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